

Features

- Extremely high speed performance
- Blocks high voltages and currents
- Two TBU® protectors in one small package
- Simple, superior circuit protection
- Minimal PCB area
- RoHS compliant*, UL Recognized 🔊

Bourns® Model P850-G Series TBU® HSPs are not recommended for P0TS applications. This series is suited for applications requiring a dual bidirectional device where 50 ohms of series resistance is acceptable. For new SLIC applications, we recommend that customers evaluate our TBU-PL Series.

P850-G Series Dual TBU® High-Speed Protectors

Transient Blocking Units - TBU® Devices

Bourns® Model P850-G TBU® products are dual high-speed bidirectional protection components, constructed using MOSFET semiconductor technology, designed to protect against faults caused by short circuits, AC power cross, induction and lightning surges.

The TBU® high speed protector, triggering as a function of the MOSFET, blocks surges and provides an effective barrier behind which sensitive electronics are not exposed to large voltages or currents during surge events. The TBU® device is provided in a surface mount DFN package and meets industry standard requirements such as RoHS and Pb Free solder reflow profiles.

Agency Approval

UL recognized component File # E315805.

Industry Standards

	Model		
Telcordia	Telcordia GR-1089 Port Type 3		P850-G
ITU-T	K.20, K.20E,	P850-G	

Absolute Maximum Ratings (T_{amb} = 25 °C)

Symbol	Parameter	Value	Unit
V _{imp}	Maximum protection voltage for impulse faults with rise time \geq 1 μ sec	850	V
V _{rms}	Maximum protection voltage for continuous V _{rms} faults	425	V
T _{op}	Operating temperature range	-40 to +85	°C
T _{stg}	Storage temperature range	-65 to +150	°C

Electrical Characteristics (T_{amb} = 25 °C)

Symbol	Parameter	Model	Min.	Тур.	Max.	Unit
I _{op}	Maximum current through the device that will not cause current blocking	P850-G120-WH P850-G200-WH			100 200	mA
I _{trigger}	Typical current for the device to go from normal operating state to protected state	P850-G120-WH P850-G200-WH		150 275		mA
l _{out}	Maximum current through the device	P850-G120-WH P850-G200-WH			200 400	mA
R _{device}	Series resistance of the TBU® device			50	55	Ω
R _{bal}	Line-to line series resistance difference between two TBU® d	levices			2	Ω
t _{block}	Maximum time for the device to go from normal operating state to protected state			1	μs	
Iquiescent	Current through the triggered TBU® device with 50 Vdc circu		0.7		mA	
V _{reset}	Voltage below which the triggered TBU® device will transition normal operating state	ı to		22		V

The P-G series TBU® devices are bidirectional; specifications are valid in both directions.

^{*}RoHS Directive 2002/95/EC Jan. 27, 2003 including annex and RoHS Recast 2011/65/EU June 8, 2011.

Specifications are subject to change without notice.

Applications

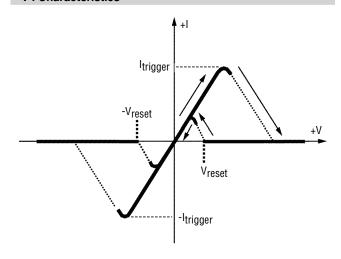
- Sensor protection
- Signal line protection

P850-G Series Dual TBU® High-Speed Protectors

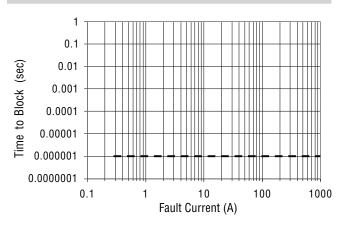
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Typical Performance Characteristics

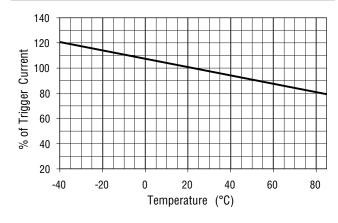
V-I Characteristics



Time to Block vs. Fault Current



Trigger Current Temperature

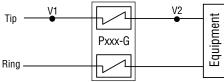


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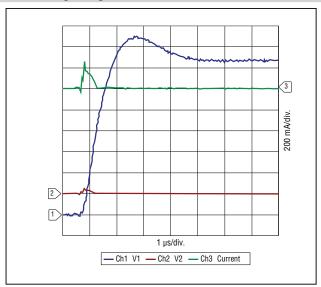
Operational Characteristics

The graphs below demonstrate the operational characteristics of the TBU® device. For each graph the fault voltage, protected side voltage, and current is presented.

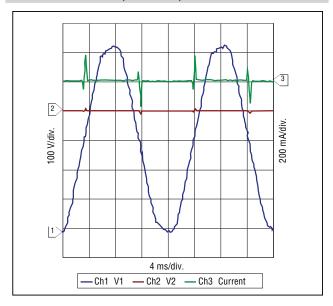
TEST CONFIGURATION DIAGRAM



P850-G Lightning, 850 V

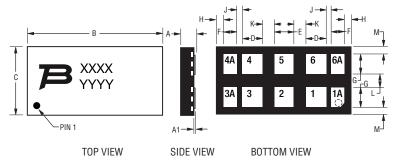


P850-G Power Fault, 230 Vrms, 25 A



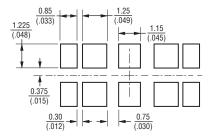
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Product Dimensions



Pads 1A and 1 are internally connected; the same for pads 3A with 3, 4A with 4, and 6A with 6. This allows for one PCB layout to accommodate the Model P850.

Recommended Pad Layout



Pad I	Designation
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Pad #	Apply	Pad #	Apply
1A	Tip In	4A	Ring Out
1	Tip In	4	Ring Out
2	NC	5	NC
3	Tip Out	6	Ring In
3A	Tip Out	6A	Ring In

NC = Solder to PCB; do not make electrical connection, do not connect to ground.

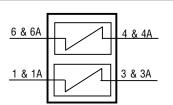
TBU® devices have matte-tin termination finish. Suggested layout should use non-solder mask define (NSMD). Recommended stencil thickness is 0.10-0.12 mm (.004-.005 in.) with stencil opening size 0.025 mm (.0010 in.) less than the device pad size. As when heat sinking any power device, it is recommended that, wherever possible, extra PCB copper area is allowed. For minimum parasitic capacitance, do not allow any signal, ground or power signals beneath any of the pads of the device.

Thermal Resistances

Part #	Symbol	Parameter	Value	Unit
P850-G	D	Junction to leads (package)	119	°C/W
P650-G	R _{th(j-a)}	Junction to leads (per TBU® device)	215	°C/W

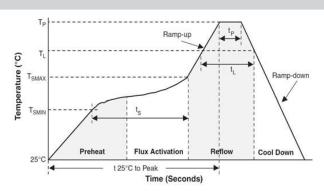
Dim.		P850-G		
Dim.	Min.	Тур.	Max.	
Α	0.80	0.90	1.00	
	(.031)	(.035)	(.039)	
A1	0.00	0.025	0.05	
	(.000)	(.001)	(.002)	
В	<u>8.15</u>	8.25	8.35	
	(.321)	(.325)	(.329)	
С	3.90	4.00	4.10	
	(0.154)	(0.157)	(0.161)	
D	1.15	1.25	1.35	
	(.045)	(.049)	(.053)	
Е	1.05	1.15	1.25	
	(.041)	(.045)	(.049)	
F	0.725	0.825	0.925	
	(.029)	(.032)	(.036)	
G	1.10	1.20	1.30	
	(.043)	(.047)	(.051)	
Н	0.375	0.425	0.475	
	(.015)	(.017)	(.019)	
J	0.25	0.30	0.35	
	(.010)	(.012)	(.014)	
K	0.70	<u>0.75</u>	<u>0.80</u>	
	(.028)	(.030)	(.031)	
L	<u>0.70</u>	<u>0.75</u>	<u>0.80</u>	
	(.028)	(.030)	(.031)	
М	0.375	0.425	0.475	
	(.015)	(.017)	(.018)	

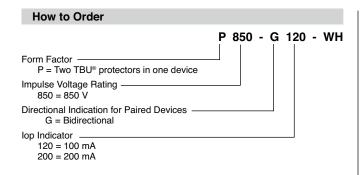
Block Diagram



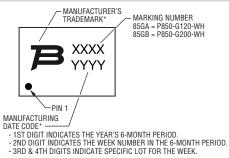
Reflow Profile

Profile Feature	Pb-Free Assembly
Average Ramp-Up Rate (Tsmax to Tp)	3 °C/sec. max.
Preheat	
- Temperature Min. (Tsmin)	150 °C
- Temperature Max. (Tsmax)	200 °C
- Time (tsmin to tsmax)	60-180 sec.
Time maintained above:	
- Temperature (TL)	217 °C
- Time (tL)	60-150 sec.
Peak/Classification Temperature (Tp)	260 °C
Time within 5 °C of Actual Peak Temp. (tp)	20-40 sec.
Ramp-Down Rate	6 °C/sec. max.
Time 25 °C to Peak Temperature	8 min. max.





Typical Part Marking

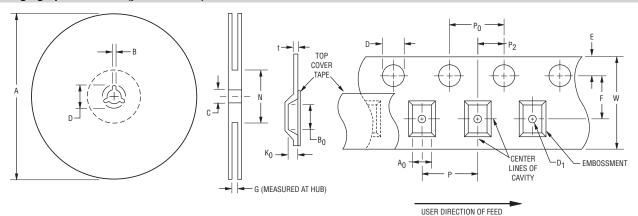


6-MONTH PERIOD CODES: A = JAN-JUN 2009 B = JUL-DEC 2009 6: C = JAN-JUN 2010 D = JUL-DEC 2010 E = JAN-JUN 2011 F = JUL-DEC 2011

- EXAMPLE: ARBC 1ST DIGIT 'A' = JAN-JUN 2009 2ND DIGIT 'R' = WEEK 18; WEEK OF APRIL 27 3RD & 4TH DIGITS 'BC' = LOT SPECIFIC INFORMATION

*TRANSITION FROM FULTEC TRADEMARK AND LOT CODE TO BOURNS TRADEMARK AND DATE CODE IN 2009.

Packaging Specifications (per EIA468-B)



QUANTITY: 3000 PIECES PER REEL

A		E	3	С		ı	D	G	N
Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Ref.	Ref.
326	330.25	1.5	2.5	12.8	13.5	20.2		16.5	102
(12.835)	(13.002)	$\overline{(.059)}$	(.098)	(.504)	(.531)	(.795)	_	(.650)	(4.016)

Α	40	В	80	I	D)1	l l	E	ı	=
Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	max.
4.2 (.165)	4.4 (.173)	8.45 (.333)	8.65 (.341)	1.5 (.059)	1.6 (.063)	1.5 (.059)	-	1.65 (.065)	1.85 (.073)	7.4 (.291)	7.6 (.299)
K	0	I	•	F	90	P	2		t	V	٧
Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.
1.1	1.3	7.9	8.1	3.9	4.1	_1.9_	2.1	0.25	0.35	15.7	16.3
(.043)	(.051)	(.311)	(.319)	(.159)	(.161)	(.075)	(.083)	(.010)	(.014)	(.618)	(.642)

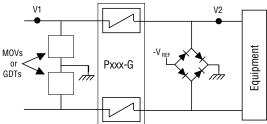
DIMENSIONS: (INCHES)

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Reference Designs

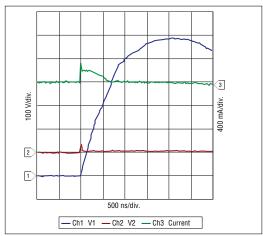
A cost-effective protection solution combines the Bourns® TBU® protection device with a pair of MOVs or Bourns® GDTs and a diode bridge. The diagram below illustrates a common configuration of these components. The graphs to the right demonstrate the operational characteristics of the circuit.

For new SLIC applications, we recommend that customers evaluate our new TBU-PL series.



Common Configuration Diagram

P850-G Con	P850-G Configuration (ITU-T K.20, K.21, K.20E, K.21E, K.45)								
Product	Qty.	Part Number	Source						
TBU® Device	1	P850-G120-WH	Bourns, Inc.						
MOV	2	MOV-10D361K	Bourns, Inc.						
Diode bridge	2	GSD2004S-V MMBD2004S	Vishay Diodes Inc.						



P850-G Solution: 4000 V Lightning 10/700 µsec, 100 A

BOURNS®

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